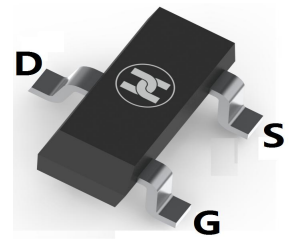
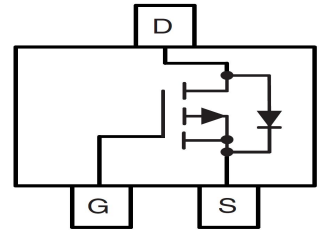


LOW VOLTAGE MOSFET (P-CHANNEL)
FEATURES

- $V_{DS}=-40V, R_{DS(ON)} \leq 96m\Omega @ V_{GS}=-10V, I_D=-3.0A$
- Low on-resistance
- For DC to DC converter and Load switch applications
- Surface Mount device


SOT-23

MECHANICAL DATA

- Case: SOT-23
- Case Material: Molded Plastic. UL flammability
- Classification Rating: 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Weight: 0.008 grams (approximate)

MAXIMUM RATINGS ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	-40	V
Gate-source voltage	V_{GS}	± 20	V
Continuous drain current ($T_J = 150^\circ C$)	I_D	$T_A = 25^\circ C$	-3.5
		$T_A = 70^\circ C$	-2.8
Pulsed drain current	I_{DM}	-20	A
Continuous Source-Drain Diode current	I_S	-1.4	A
Power dissipation	P_D	$T_A = 25^\circ C$	1.25
		$T_A = 70^\circ C$	0.81
Thermal resistance from Junction to ambient	$R_{\theta JA}$	105	$^\circ C/W$
Junction temperature	T_J	150	$^\circ C$
Storage temperature	T_{STG}	-55 ~ +150	$^\circ C$

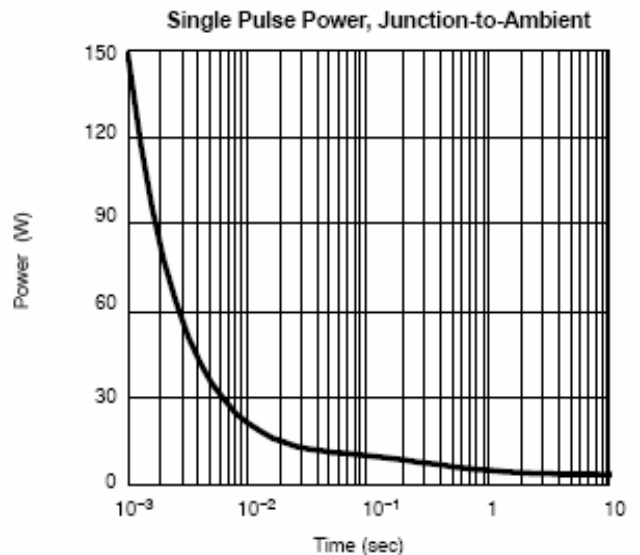
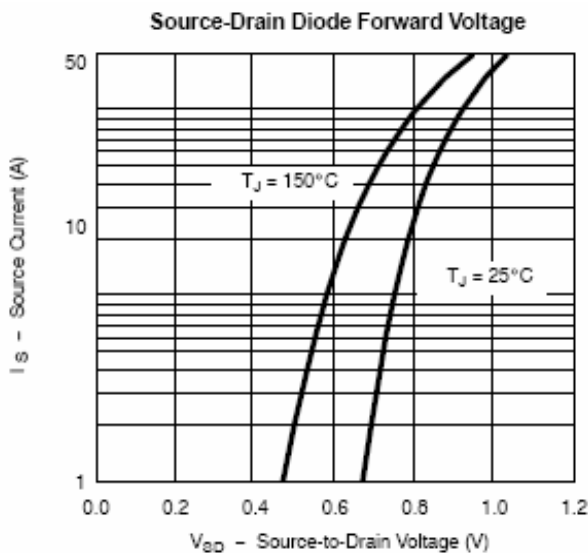
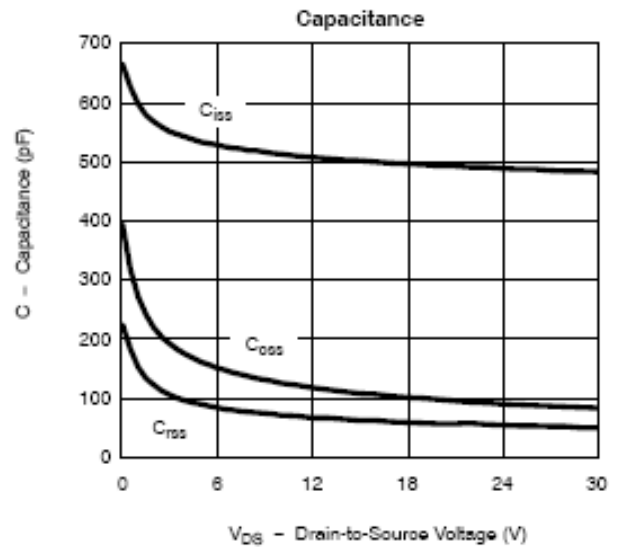
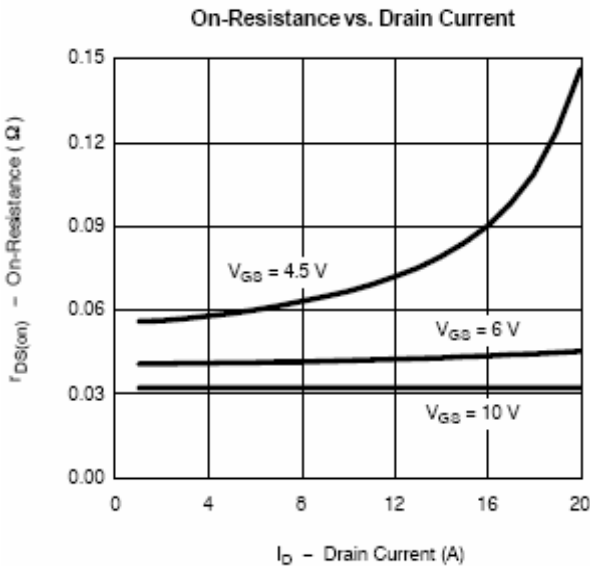
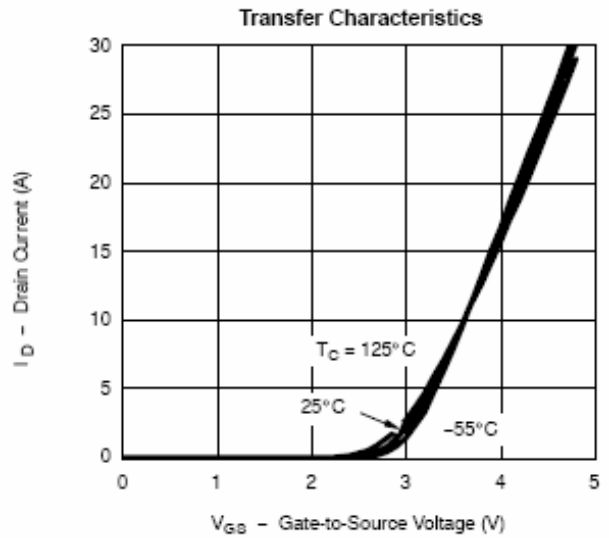
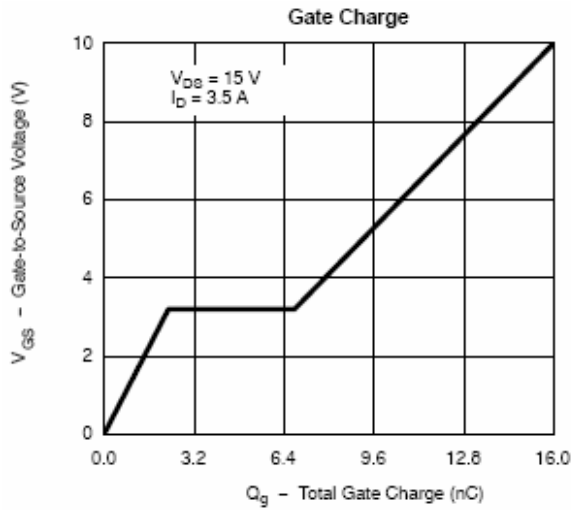
ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ C$ unless otherwise specified)

Parameter	Symbo	Min	Typ	Max	Unit	Conditions
Drain-Source breakdown voltage	$V_{(BR)DSS}$	-40			V	$V_{GS}=0V, I_D=-250\mu A$
Zero gate voltage drain current	I_{DSS}			-1	μA	$V_{DS}=-36V, V_{GS}=0V$
				-5	μA	$V_{DS}=-36V, V_{GS}=0V, T_J = 85^\circ C$
Gate-body leakage current	I_{GSS}			± 100	nA	$V_{DS}=0V, V_{GS}=\pm 20V$
Gate-threshold voltage(note 1)	$V_{GS(th)}$	-0.8		-2.5	V	$V_{DS}=V_{GS}, I_D=-250\mu A$
Drain-source on-resistance (note 1)	$R_{DS(ON)}$		90	96	m Ω	$V_{GS}=-10V, I_D=-3.0A$
			100	110	m Ω	$V_{GS}=-4.5V, I_D=-2.8A$
Forward transconductance (note 1)	g_{FS}		13		S	$V_{DS}=-15V, I_D=-3.0A$
Input capacitance(note 1)	C_{iss}		500		pF	$V_{DS}=-15V, V_{GS}=0V, f=1MHz$
Output capacitance(note 1)	C_{oss}		95		pF	
Reverse transfer capacitance(note 1)	C_{rss}		50		pF	
Turn-on delay time(note 1)	$t_{d(on)}$		8	20	nS	$V_{DD}=-15V, I_D=-1A, V_{GEN}=-4.5V, R_g=6\Omega$
Turn-on rise time(note 1)	t_r		10	20	nS	
Turn-off delay time(note 1)	$t_{d(off)}$		30	35	nS	
Turn-off fall time(note 1)	t_f		15	20	nS	$V_{DS}=-15V, V_{GS}=-10V, I_D=-3.0A$
Total gate charge(note 1)	Q_g		9	12	nC	
Gate-source charge(note 1)	Q_{gs}		1.5		nC	
Gate-drain charge(note 1)	Q_{gd}		2.0		nC	$I_S=-1.3A, V_{GS}=0V$
Diode forward voltage (note 1)	V_{SD}		-0.55	-1.0	V	

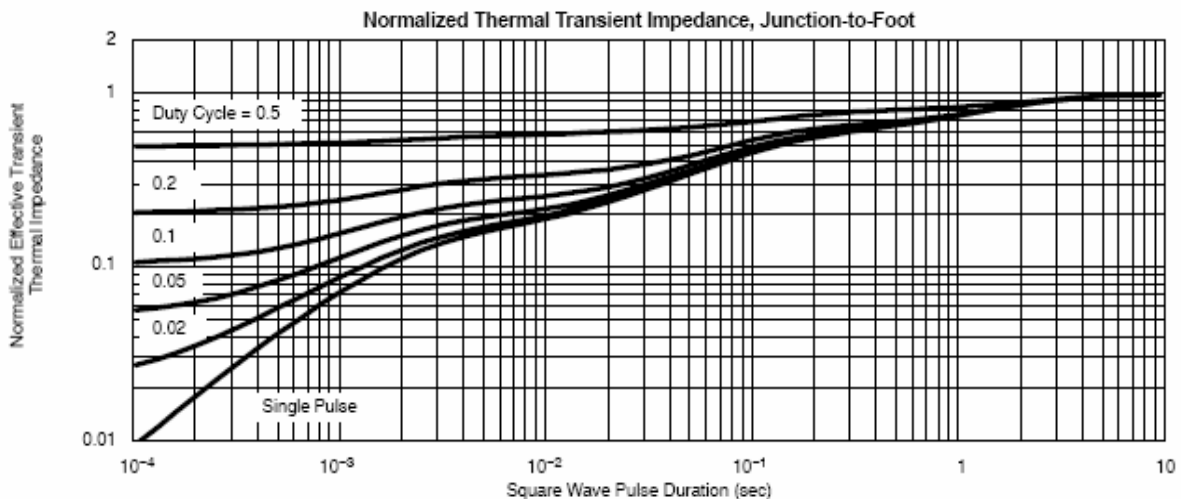
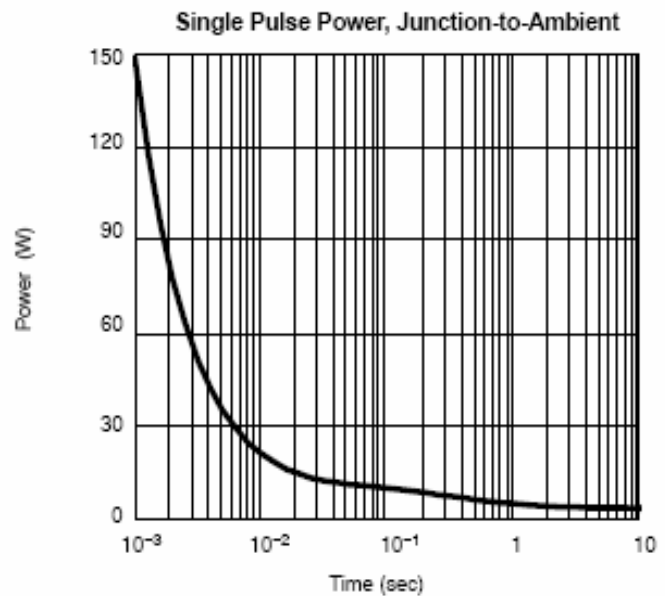
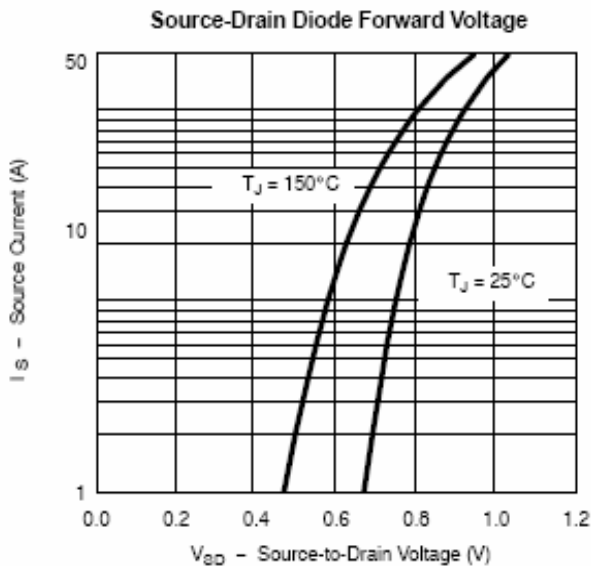
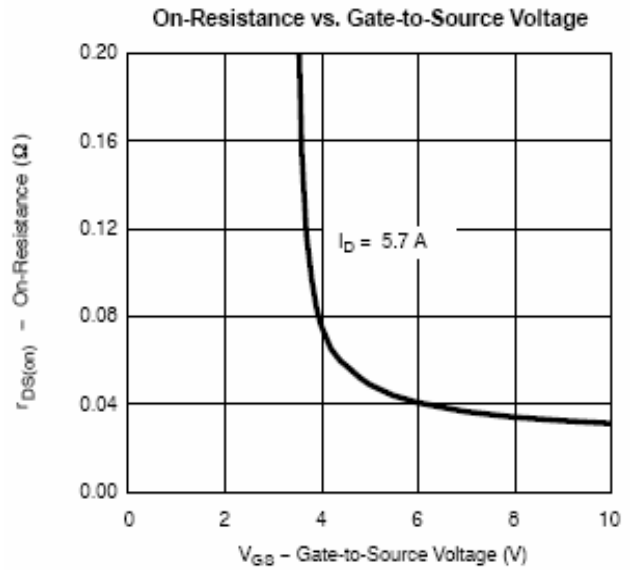
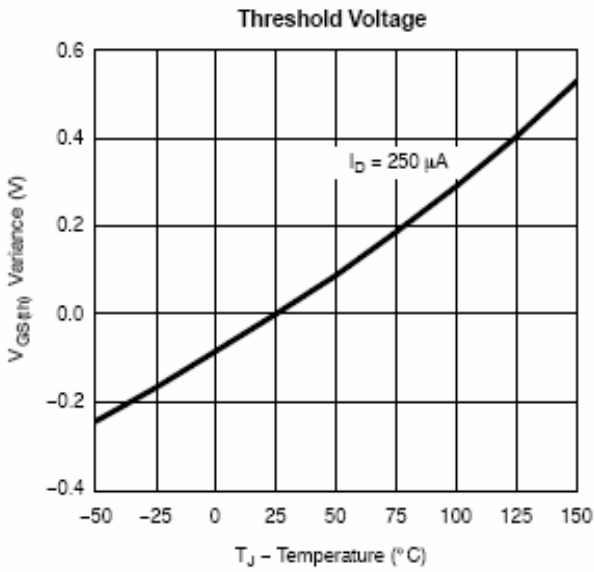
Note:1. Pulse test ; Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

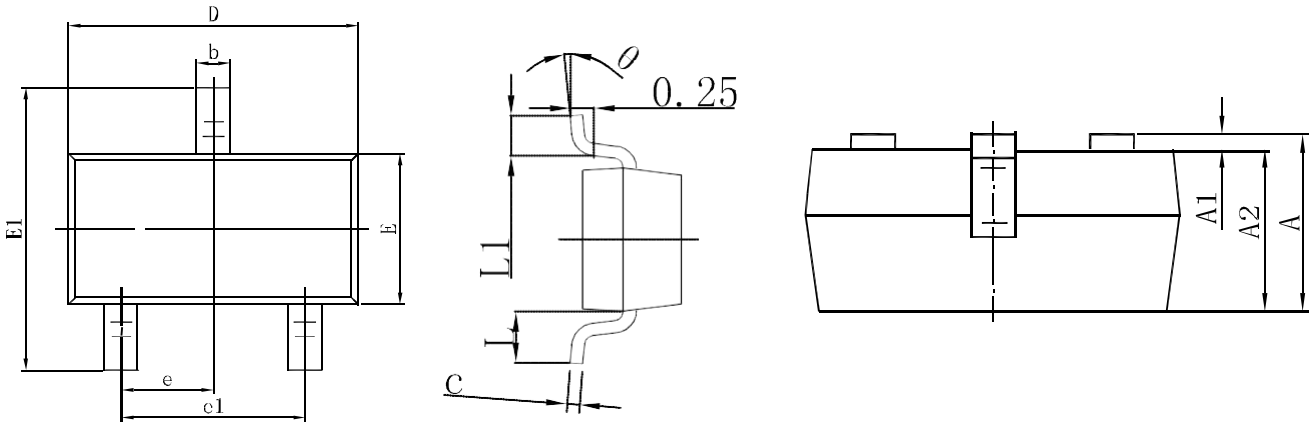
LOW VOLTAGE MOSFET (P-CHANNEL)

Typical Characteristics

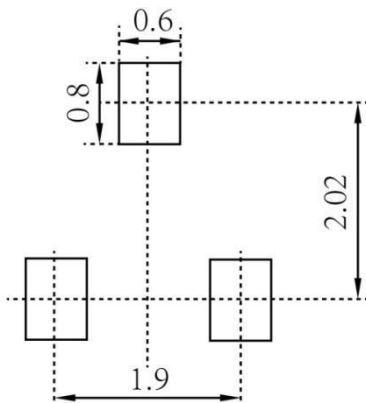


LOW VOLTAGE MOSFET (P-CHANNEL)



LOW VOLTAGE MOSFET (P-CHANNEL)
SOT-23 Package Outline Dimensions


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

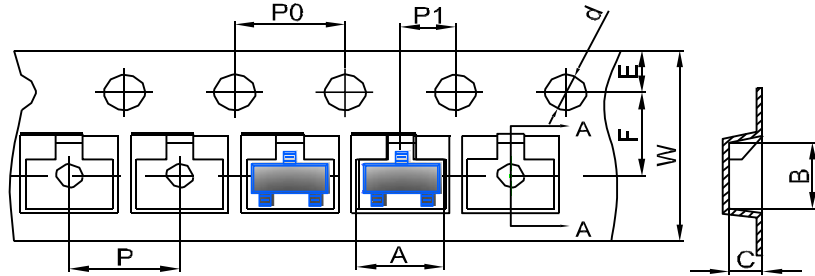
SOT-23 Suggested Pad Layout

Note:

1. Controlling dimension: in millimeters
2. General tolerance: $\pm 0.05\text{mm}$
3. The pad layout is for reference purposes only

LOW VOLTAGE MOSFET (P-CHANNEL)

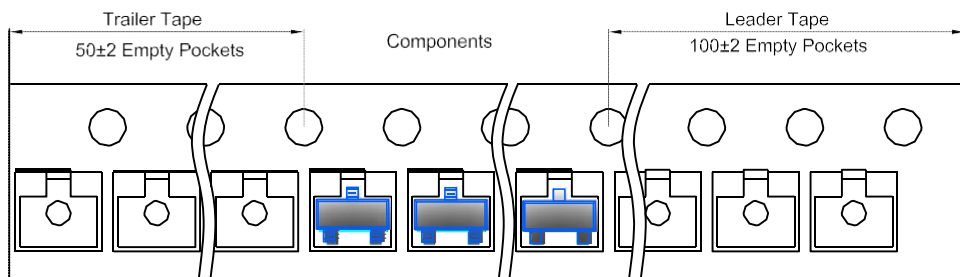
SOT-23 Tape and Reel

SOT-23 Embossed Carrier Tape

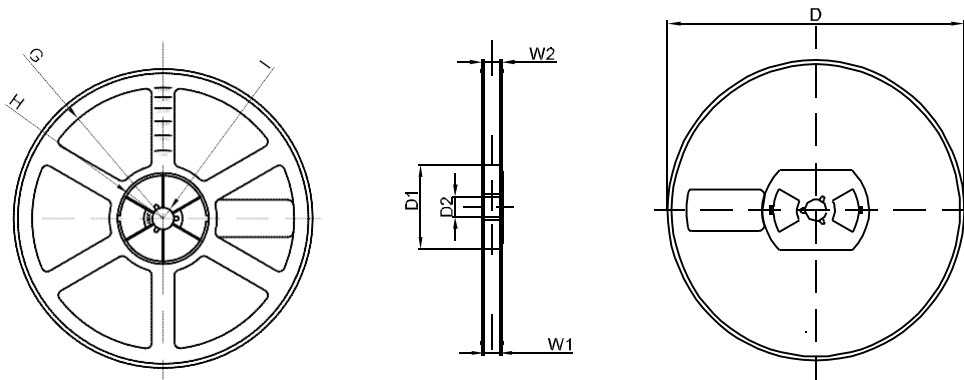


DIMENSIONS ARE IN MILLIMETER										
TYPE	A	B	C	d	E	F	P0	P	P1	W
SOT-23	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00
TOLERANCE	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1

SOT-23 Tape Leader and Trailer



SOT-23 Reel



DIMENSIONS ARE IN MILLIMETER								
REEL OPTION	D	D1	D2	G	H	I	W1	W2
7" DIA	Ø178	54.40	13.00	R78	R25.60	R6.50	9.50	12.30
TOLERANCE	±2	±1	±1	±1	±1	±1	±1	±1